

2021 20th International Workshop on Junction Technology (IWJT 2021)

**Kyoto, Japan
10-11 June 2021**



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IWJT2021, Through on-line, June 10-11, 2021

June 10 (Thursday)

9:45 **Opening Remarks**

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10:00 KN-1 **HfO_x based Ferroelectric Materials and Memories** 1
Ming Liu / Chinese Academy of Sciences

10:40 **Break (10 min)**

Session 1 Junction Technology for Memory

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[Invited] Jun Okuno / Sony Semiconductor Solutions Corp.

11:20 S1-2 **Fabrication and Evaluation of Split-Gate Type Charge-Trapping
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[Invited] Yanzhe Wang / Renesas Electronics Corp.

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Kazunari Ishimaru / Kioxia Corp.

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[Invited] Kazunari Kurita / SUMCO Corp.

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[Invited] Yoshihiro Sato / Panasonic Corp.

14:50 S2-3 **Reduction of Process-induced damage in atomic layer etching** 25
[Invited] Akiko Hirata / Sony Semiconductor Solutions Corp.

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		Philippe Rodriguez / Univ. Grenoble Alpes, CEA-Leti	
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	[Invited]	Sébastien Kerdilès / Univ. Grenoble Alpes, CEA-Leti	
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	[Invited]	Fuccio Cristiano / LAAS-CNRS	
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		Hideaki Tanimura / SCREEN Semiconductor Solutions Co., Ltd.	
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Akshay Singh / Micron Technology, Inc.

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[Invited] Hans Van Meer / Applied Materials Inc.

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Abhijeet Joshi / Active Layer Parametrics (ALP)

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[Invited] Jing Wan / Fudan Univ.

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17:40 **Preparation for Closing and Award Ceremony**

17:50 **Closing Remarks** (Award, Invitation for next workshop)